

ESD Protection Diode

Low Capacitance ESD Protection for High Speed Data

NUP2114 Series, SNUP2114

The NUP2114 surge protection is designed to protect high speed data lines from ESD. Ultra-low capacitance and high level of ESD protection makes this device well suited for use in USB 2.0 applications.

Features

- Low Capacitance 0.8 pF
- Low Clamping Voltage
- Stand Off Voltage: 5 V
- Low Leakage
- ESD Rating of Class 3B (Exceeding 8 kV) per Human Body model and Class C (Exceeding 400 V) per Machine Model
- Protection for the Following IEC Standards:
IEC 61000-4-2 Level 4 ESD Protection
- UL Flammability Rating of 94 V-0
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- High Speed Communication Line Protection
- USB 2.0 High Speed Data Line and Power Line Protection
- Monitors and Flat Panel Displays
- MP3
- Gigabit Ethernet
- Notebook Computers
- Digital Video Interface (DVI) and HDMI

MAXIMUM RATINGS (T_J = 25 °C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature - Maximum (10 Seconds)	T _L	260	°C
Human Body Model (HBM) Machine Model (MM) IEC 61000-4-2 Contact IEC61000-4-2 Air	ESD	16000 400 13000 15000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

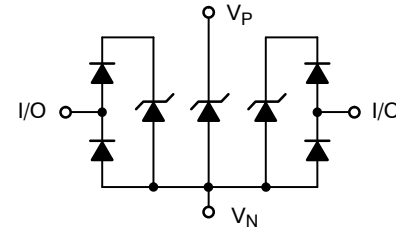
See Application Note [AND8308/D](#) for further description of survivability specs.



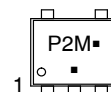
SOT-553
CASE 463B



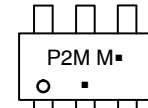
TSOP-6
CASE 318G



MARKING DIAGRAMS



SOT-553

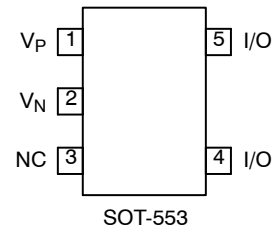


TSOP-6

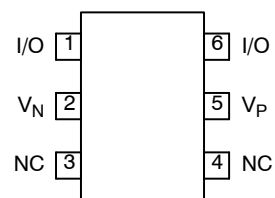
P2, P2M = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



SOT-553



TSOP-6

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

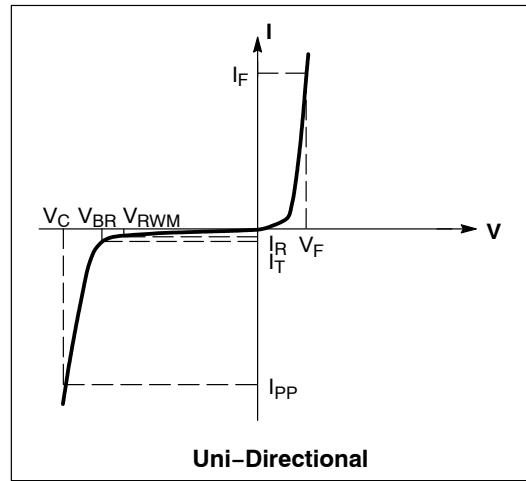
NUP2114 Series, SNUP2114

ELECTRICAL CHARACTERISTICS

($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F
P_{pk}	Peak Power Dissipation
C	Max. Capacitance @ $V_R = 0$ and $f = 1.0$ MHz

* See Application Note AND8308/D for detailed explanations of datasheet parameters.



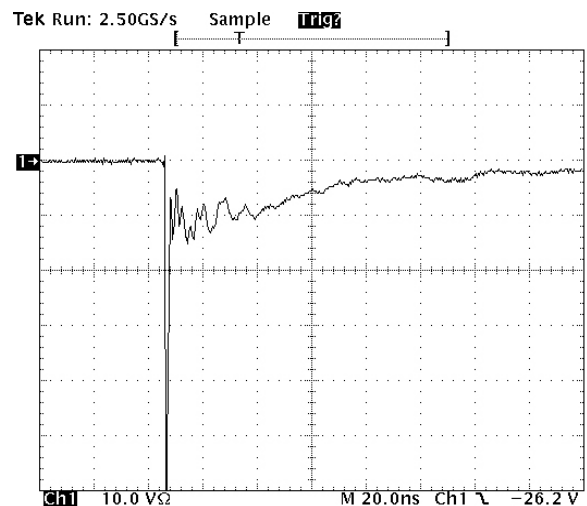
ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}	(Note 1)			5.0	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{ mA}$, (Note 2)	5.5	7.5		V
Reverse Leakage Current	I_R	$V_{RWM} = 5\text{ V}$		0.01	1.0	μA
Clamping Voltage	V_C	$I_{PP} = 5\text{ A}$ (Note 3)		9.0		V
Clamping Voltage	V_C	$I_{PP} = 8\text{ A}$ (Note 3)		10		V
Maximum Peak Pulse Current	I_{PP}	8x20 μs Waveform			12	A
Junction Capacitance	C_J	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$ between I/O Pins and GND		0.8	1.0	pF
Junction Capacitance	C_J	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$ between I/O Pins			0.5	pF
Clamping Voltage	V_C	@ $I_{PP} = 1\text{ A}$ (Note 4)			12	V
Clamping Voltage	V_C	Per IEC 61000-4-2 (Note 5)		Figures 1 and 2		V

1. Surge protection devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
2. V_{BR} is measured at pulse test current I_T .
3. Nonrepetitive current pulse (Pin 5 to Pin 2)
4. Surge current waveform per Figure 5.
5. Typical waveform. For test procedure see Figures 3 and 4 and Application Note AND8307/D.
6. Include S-prefix devices where applicable.



**Figure 1. ESD Clamping Voltage Screenshot
Positive 8 kV Contact per IEC61000-4-2**



**Figure 2. ESD Clamping Voltage Screenshot
Negative 8 kV Contact per IEC61000-4-2**

NUP2114 Series, SNUP2114

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

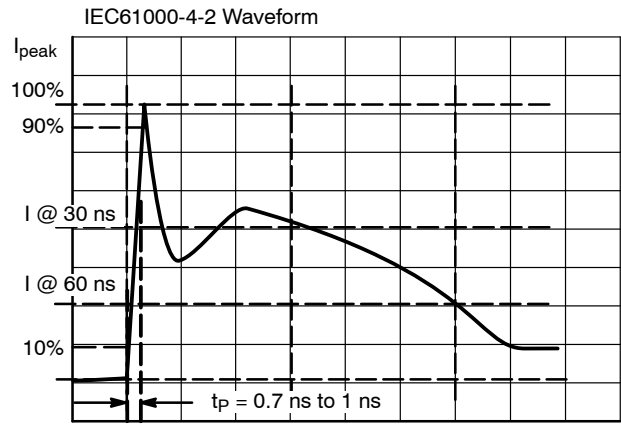


Figure 3. IEC61000-4-2 Spec

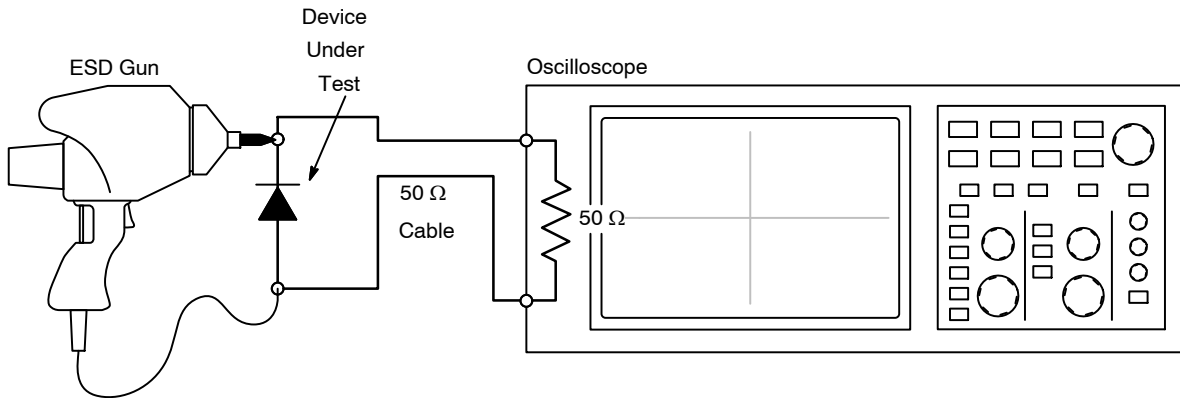


Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D - Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. **onsemi** has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how **onsemi** creates these screenshots and how to interpret them please refer to AND8307/D.

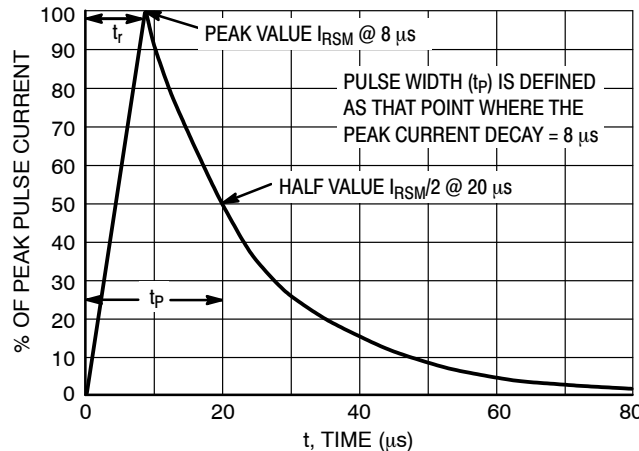


Figure 5. 8 x 20 μ s Pulse Waveform

NUP2114 Series, SNUP2114

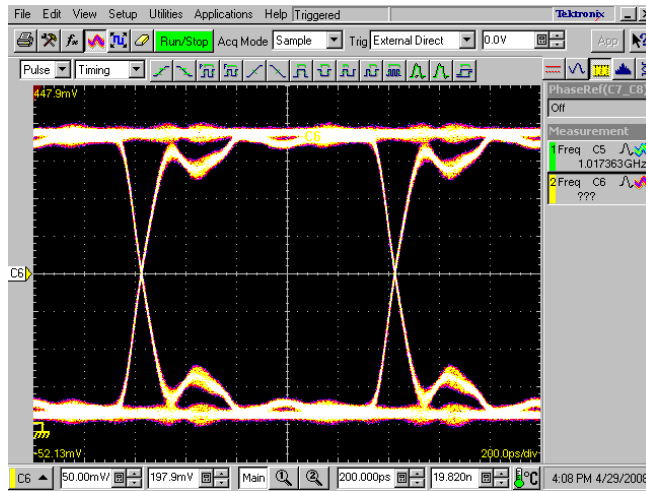


Figure 6. 500 MHz Data Pattern

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NUP2114UPXV5T1G	P2	SOT-553 (Pb-Free)	4 000 / Tape & Reel
NUP2114UCMR6T1G	P2M	TSOP-6 (Pb-Free)	3 000 / Tape & Reel
SNUP2114UCMR6T1G*	P2M	TSOP-6 (Pb-Free)	3 000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

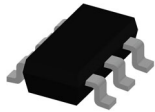
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NUP2114 Series, SNUP2114

REVISION HISTORY

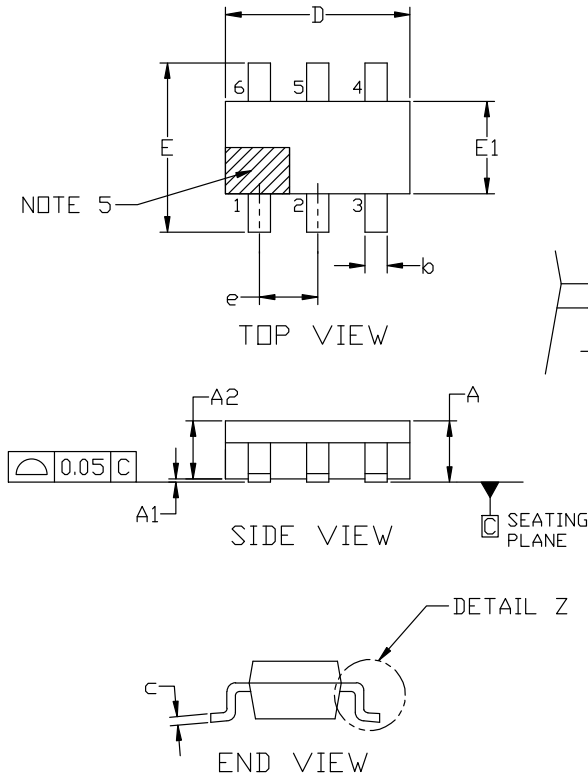
4	Rebranded the document to onsemi format.	11/24/2025
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This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.



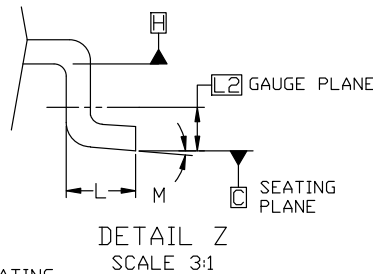
TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

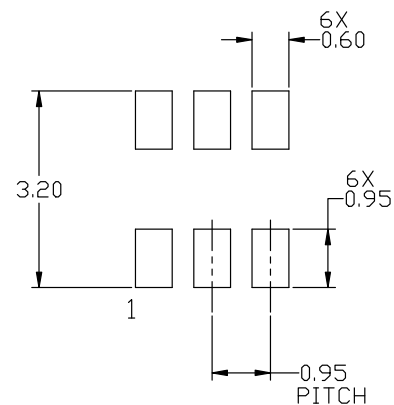


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	---	10°



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

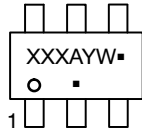
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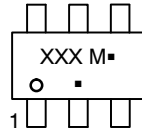
TSOP-6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024

**GENERIC
MARKING DIAGRAM***



IC



STANDARD

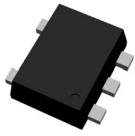
XXX = Specific Device Code	XXX = Specific Device Code
A = Assembly Location	M = Date Code
Y = Year	▪ = Pb-Free Package
W = Work Week	
▪ = Pb-Free Package	

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- | | | | | | |
|--|--|---|---|---|--|
| <p>STYLE 1:
 PIN 1. DRAIN
 2. DRAIN
 3. GATE
 4. SOURCE
 5. DRAIN
 6. DRAIN</p> | <p>STYLE 2:
 PIN 1. EMITTER 2
 2. BASE 1
 3. COLLECTOR 1
 4. EMITTER 1
 5. BASE 2
 6. COLLECTOR 2</p> | <p>STYLE 3:
 PIN 1. ENABLE
 2. N/C
 3. R BOOST
 4. Vz
 5. V in
 6. V out</p> | <p>STYLE 4:
 PIN 1. N/C
 2. V in
 3. NOT USED
 4. GROUND
 5. ENABLE
 6. LOAD</p> | <p>STYLE 5:
 PIN 1. EMITTER 2
 2. BASE 2
 3. COLLECTOR 1
 4. EMITTER 1
 5. BASE 1
 6. COLLECTOR 2</p> | <p>STYLE 6:
 PIN 1. COLLECTOR
 2. COLLECTOR
 3. BASE
 4. EMITTER
 5. COLLECTOR
 6. COLLECTOR</p> |
| <p>STYLE 7:
 PIN 1. COLLECTOR
 2. COLLECTOR
 3. BASE
 4. N/C
 5. COLLECTOR
 6. EMITTER</p> | <p>STYLE 8:
 PIN 1. Vbus
 2. D(in)
 3. D(in)+
 4. D(out)+
 5. D(out)
 6. GND</p> | <p>STYLE 9:
 PIN 1. LOW VOLTAGE GATE
 2. DRAIN
 3. SOURCE
 4. DRAIN
 5. DRAIN
 6. HIGH VOLTAGE GATE</p> | <p>STYLE 10:
 PIN 1. D(OUT)+
 2. GND
 3. D(OUT)-
 4. D(IN)-
 5. VBUS
 6. D(IN)+</p> | <p>STYLE 11:
 PIN 1. SOURCE 1
 2. DRAIN 2
 3. DRAIN 2
 4. SOURCE 2
 5. GATE 1
 6. DRAIN 1/GATE 2</p> | <p>STYLE 12:
 PIN 1. I/O
 2. GROUND
 3. I/O
 4. I/O
 5. VCC
 6. I/O</p> |
| <p>STYLE 13:
 PIN 1. GATE 1
 2. SOURCE 2
 3. GATE 2
 4. DRAIN 2
 5. SOURCE 1
 6. DRAIN 1</p> | <p>STYLE 14:
 PIN 1. ANODE
 2. SOURCE
 3. GATE
 4. CATHODE/DRAIN
 5. CATHODE/DRAIN
 6. CATHODE/DRAIN</p> | <p>STYLE 15:
 PIN 1. ANODE
 2. SOURCE
 3. GATE
 4. DRAIN
 5. N/C
 6. CATHODE</p> | <p>STYLE 16:
 PIN 1. ANODE/CATHODE
 2. BASE
 3. EMITTER
 4. COLLECTOR
 5. ANODE
 6. CATHODE</p> | <p>STYLE 17:
 PIN 1. EMITTER
 2. BASE
 3. ANODE/CATHODE
 4. ANODE
 5. CATHODE
 6. COLLECTOR</p> | |

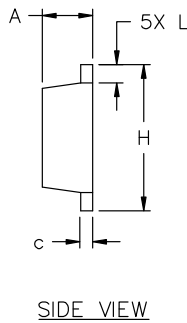
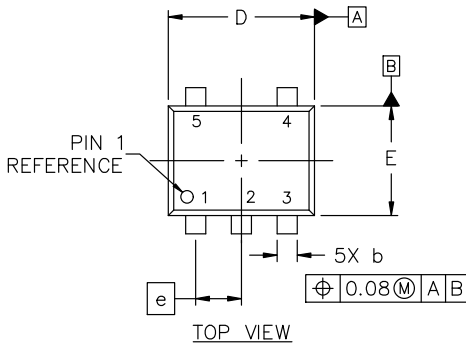
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CASE 463B
ISSUE D

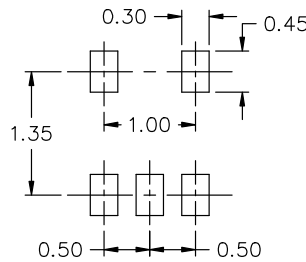
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NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.55	1.60	1.65
E	1.15	1.20	1.25
e	0.50 BSC		
H	1.55	1.60	1.65
L	0.10	0.20	0.30



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

- STYLE 2:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

- STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

- STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

- STYLE 5:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

- STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR 1
5. COLLECTOR 2/BASE 1

- STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

- STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

- STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE

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